



# AMENDMENT TRANSMITTAL LETTER

Docket No.  
M4065.0315/P315

Application No.  
09/651,998

Filing Date  
August 31, 2000

Examiner  
H. Tsai

Art Unit  
2812

Applicant(s): Er-Xuan Ping, et al.

Invention: METHOD AND STRUCTURE FOR REDUCING LEAKAGE CURRENT IN CAPACITORS

## TO THE COMMISSIONER FOR PATENTS

Transmitted herewith is an amendment in the above-identified application.

The fee has been calculated and is transmitted as shown below.

CLAIMS AS AMENDED					
	Claims Remaining After Amendment	Highest Number Previously Paid	Number Extra Claims Present	Rate	
Total Claims	38	- 95 =	0	x	\$0.00
Independent Claims	5	- 7 =	0	x	\$0.00
Multiple Dependent Claims (check if applicable) <input type="checkbox"/>					
Other fee (please specify):					
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT:					\$0.00

☒ Large Entity

☐ Small Entity

☐ No additional fee is required for this amendment.

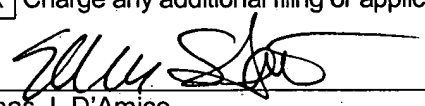
☒ Please charge Deposit Account No. 04-1073 in the amount of \$ \$290.00  
A duplicate copy of this sheet is enclosed.

☐ A check in the amount of \$ \_\_\_\_\_ to cover the filing fee is enclosed.

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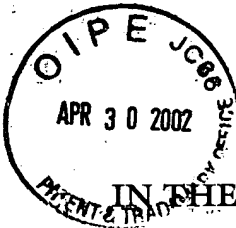
☐ Credit any overpayment.

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Dated: April 30, 2002

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Docket No.: M4065.0315 / P317dtb  
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:  
Er-Xuan Ping, et al.

Application No.: 09/651,998.

Group Art Unit: 2812

Filed: August 31, 2000

Examiner: H. Tsai

For: METHOD AND STRUCTURE FOR  
REDUCING LEAKAGE CURRENT IN  
CAPACITORS

**SECOND AMENDMENT UNDER 37 CFR 1.116  
AND REQUEST FOR RECONSIDERATION**

Box AF  
Commissioner for Patents  
Washington, DC 20231

Dear Sir:

In response to the Office Action dated November 30, 2001 (Paper No. 9), finally rejecting claims 1-95, and pursuant to the Advisory Action mailed April 9, 2002, please amend the above-identified U.S. Patent application as follows:

**In the Claims**

Please cancel claims 2, 43, and 60-95 without prejudice.

1. (Amended) A method of forming a capacitor on a substrate in a semiconductor device, comprising:

forming a first layer of a conductive material over said substrate;

forming a second layer of a dielectric over said first layer, said second layer having a thickness not exceeding about 60 Angstroms;

\* two identical  
copies of claims,  
no mark up  
copy. HST \*